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Listing of Claims

This listing of claims will replace all prior versions and listings of claims in the application:

- 1. (currently amended) A method, comprising:
- exposing a surface region of a layer of a first material having a first chemical composition to at least one ion beam in an environment comprising a reactive species to biaxially texture the surface region of the layer and to change the composition of the layer in the surface region to a second material having a second chemical composition different than the first chemical composition.
- 2. (original) The method of claim 1, wherein the at least one ion beam is two ion beams.
- 3. (original) The method of claim 1, wherein the at least one ion beam is three ion beams.
- 4 (original) The method of claim 1, wherein the at least one ion beam is four ion beams.
- 5. (original) The method of claim 1, wherein the at least one ion beam comprises at least five ion beams.
- 6. (original) The method of claim 1, wherein the reactive species comprises oxygen.

- 7. (original) The method of claim 1, wherein the reactive species comprises nitrogen.
- 8. (original) The method of claim 1, wherein the surface region has a depth of less than about 50 nanometers.
- (original) The method of claim 8, wherein the depth of the surface region is at least about five nanometers.
- 10. (original) The method of claim 1, wherein the first material comprises a nitride and the second material composition comprises an oxide.
- 11. (original) The method of claim 1, wherein the first material composition comprises a material selected from the group consisting of vanadium nitride, zirconium nitride, titanium nitride and cerium nitride.
- 12. (original) The method of claim 11, wherein the second material composition comprises a material selected from the group consisting of vanadium oxide, zirconium oxide, titanium oxide and cerium oxide.
- 13. (original) The method of claim 1, wherein, prior to exposure to the at least one ion beam, the surface region is noncrystalline.

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14. (cancelled)

- 15. (currently amended) The method of claim 1, wherein the at least one ion beam comprises two ion beams that impinge on the surface region of the layer at a first angle relative to a perpendicular to the surface of the layer, and the two ion beams are disposed relative to each other at a second angle so that the <u>biaxially</u> textured surface region has a crystal plane that is oriented perpendicular to the <u>biaxially</u> textured surface.
- 16. (original) The method of claim 1, further comprising exposing the second material to the reactive species in the absence of the at least one ion beam.
- 17. (original) The method of claim 16, wherein the second material is exposed to the reactive species in the absence of the at least one ion beam at a temperature greater than room temperature.
- 18. (currently amended) A method of ion texturing a noncrystalline surface of a layer of a nitride, the method comprising:

exposing a surface region of a layer of the nitride to at least two ion beams in an environment comprising a reactive species to <u>biaxially</u> texture the surface region of the layer and to change the composition of the layer in the surface region to an oxide to form a <u>biaxially</u> textured oxide surface.

- 19. (currently amended) The method of claim 18, wherein the at least two ion beams impinge on the surface region at a first angle relative to a perpendicular to the surface, and the at least two ion beams are disposed relative to each other at a second angle so that a crystal plane of the <u>biaxially</u> textured surface region is oriented perpendicular to the <u>biaxially</u> textured oxide surface.
- (original) The method of claim 18, wherein the reactive species comprises oxygen.
- 21. (original) The method of claim 18, wherein the surface region of the oxide has a depth of less than about 50 nanometers.
- 22. (original) The method of claim 21, wherein the depth of the surface region of the oxide is at least about five nanometers.
- 23. (original) The method of claim 18, wherein the nitride is selected from the group consisting of vanadium nitride, zirconium nitride, titanium nitride and cerium nitride.
- 24. (original) The method of claim 23, wherein the oxide is selected from the group consisting of vanadium oxide, zirconium oxide, titanium oxide and cerium oxide.
- 25. (original) The method of claim 18, wherein the oxide is selected from the group consisting of vanadium oxide, zirconium oxide, titanium oxide and cerium oxide.

- 26. (original) The method of claim 18, further comprising exposing the second material to a reactive species in the absence of the at least two ion beams.
- 27. (original) The method of claim 26, wherein the oxide material is exposed to the reactive species in the absence of the at least two ion beams at a temperature greater than room temperature.